## UT54ACTS00E

## Quadruple 2-Input NAND Gates

April 2015
www.aeroflex.com/Logic
Datasheet

## FEATURES

- $0.6 \mu \mathrm{~m}$ CRH CMOS process
- Latchup immune
- High speed
- Low power consumption
- Wide power supply operating range from 3.0 V to 5.5 V
- Available QML Q or V processes
- 14-lead flatpack
- UT54ACTS00E - SMD 5962-96513


## DESCRIPTION

The UT54ACTS00E is a performance and voltage enhanced version of the UT54ACTS00 quadruple, two-input NAND gate. The circuit performs the Boolean functions $\mathrm{Y}=\overline{\mathrm{A} \cdot \mathrm{B}}$ or $\mathrm{Y}=\overline{\mathrm{A}}$ $+\overline{\mathrm{B}}$ in positive logic.

The device is characterized over full military temperature range of $-55^{\circ} \mathrm{C}$ to $+125^{\circ} \mathrm{C}$.

## FUNCTION TABLE

| INPUTS |  | OUTPUT |
| :---: | :---: | :---: |
| A | B | $Y$ |
| $H$ | $H$ | L |
| L | $X$ | $H$ |
| $X$ | L | $H$ |

## PINOUT

14-Lead Flatpack
TopView


## LOGIC SYMBOL



## Note:

1. Logic symbol in accordance with ANSI/IEEE standard 91-1984 and IEC Publication 617-12

## LOGIC DIAGRAM



OPERATIONAL ENVIRONMENT ${ }^{1}$

| PARAMETER | LIMIT | UNITS |
| :---: | :---: | :---: |
| Total Dose | 1.0 E 6 | $\mathrm{rads}(\mathrm{Si})$ |
| SEU Threshold $^{2}$ | 108 | $\mathrm{MeV}-\mathrm{cm}^{2} / \mathrm{mg}$ |
| SEL Threshold | 120 | $\mathrm{MeV}-\mathrm{cm}^{2} / \mathrm{mg}$ |
| Neutron Fluence | 1.0 E 14 | $\mathrm{n} / \mathrm{cm}^{2}$ |

Notes:

1. Logic will not latchup during radiation exposure within the limits defined in the table.
2. Device storage elements are immune to SEU affects.

ABSOLUTE MAXIMUM RATINGS ${ }^{1}$

| SYMBOL | PARAMETER | LIMIT | UNITS |
| :---: | :---: | :---: | :---: |
| $\mathrm{V}_{\mathrm{DD}}$ | Supply voltage | -0.3 to 7.0 | V |
| $\mathrm{~V}_{\mathrm{I} / \mathrm{O}}$ | Voltage any pin | -0.3 to $\mathrm{V}_{\mathrm{DD}}+0.3$ | V |
| $\mathrm{~T}_{\mathrm{STG}}$ | Storage Temperature range | -65 to +150 | ${ }^{\circ} \mathrm{C}$ |
| $\mathrm{T}_{\mathrm{J}}$ | Maximum junction temperature | +175 | ${ }^{\circ} \mathrm{C}$ |
| $\mathrm{T}_{\mathrm{LS}}$ | Lead temperature (soldering 5 seconds | +300 | ${ }^{\circ} \mathrm{C}$ |
| $\Theta_{\mathrm{JC}}$ | Thermal resistance junction to case | 15 | ${ }^{\circ} \mathrm{C} / \mathrm{W}$ |
| $\mathrm{I}_{\mathrm{I}}$ | DC input current | $\pm 10$ | mA |
| $\mathrm{P}_{\mathrm{D}}{ }^{2}$ | Maximum package power dissipation |  |  |
|  | permitted @ $\mathrm{T}_{\mathrm{C}}=+125^{\circ} \mathrm{C}$ | 3.2 | W |

Note:

1. Stresses outside the listed absolute maximum ratings may cause permanent damage to the device. This is a stress rating only, functional operation of the device at these or any other conditions beyond limits indicated in the operational sections is not recommended. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.
2. Per MIL-STD-883, method 1012.1, Section 3.4.1, $P_{D}=\left(T_{J(\max )}-T_{C(\max )}\right) / \Theta_{J C}$

## RECOMMENDED OPERATING CONDITIONS

| SYMBOL | PARAMETER | LIMIT | UNITS |
| :---: | :---: | :---: | :---: |
| $\mathrm{V}_{\mathrm{DD}}$ | Supply voltage | 3.0 to 5.5 | V |
| $\mathrm{~V}_{\mathrm{IN}}$ | Input voltage any pin | 0 to $\mathrm{V}_{\mathrm{DD}}$ | V |
| $\mathrm{T}_{\mathrm{C}}$ | Temperature range | -55 to +125 | ${ }^{\circ} \mathrm{C}$ |

DC ELECTRICAL CHARACTERISTICS FOR THE UT54ACTS00E ${ }^{7}$
$\left(\mathrm{V}_{\mathrm{DD}}=3.0 \mathrm{~V}\right.$ to $\left.5.5 \mathrm{~V} ; \mathrm{V}_{\mathrm{SS}}=0 \mathrm{~V}^{6} ;-55^{\circ} \mathrm{C}<\mathrm{T}_{\mathrm{C}}<+125^{\circ} \mathrm{C}\right)$

| SYMBOL | DESCRIPTION | CONDITION | MIN | MAX | UNIT |
| :---: | :---: | :---: | :---: | :---: | :---: |
| $\mathrm{V}_{\text {IL1 }}$ | Low-level input voltage ${ }^{1}$ | $\mathrm{V}_{\mathrm{DD}}$ from 4.5 V to 5.5 V |  | 0.8 | V |
| $\mathrm{V}_{\text {IL2 }}$ | Low-level input voltage ${ }^{1}$ | $\mathrm{V}_{\mathrm{DD}}$ from 3.0 V to 3.6 V |  | 0.8 | V |
| $\mathrm{V}_{\mathrm{IH} 1}$ | High-level input voltage ${ }^{1}$ | $\mathrm{V}_{\mathrm{DD}}$ from 4.5 V to 5.5 V | $0.5 \mathrm{~V}_{\mathrm{DD}}$ |  | V |
| $\mathrm{V}_{\mathrm{IH} 2}$ | High-level input voltage ${ }^{1}$ | $\mathrm{V}_{\mathrm{DD}}$ from 3.0V to 3.6 V | 2.0 |  | V |
| $\mathrm{I}_{\text {IN }}$ | Input leakage current | $\mathrm{V}_{\text {IN }}=\mathrm{V}_{\text {DD }}$ or $\mathrm{V}_{\text {SS }}$ | -1 | 1 | $\mu \mathrm{A}$ |
| $\mathrm{V}_{\text {OL1 }}$ | Low-level output voltage 3 | $\begin{aligned} & \mathrm{I}_{\mathrm{OL}}=8 \mathrm{~mA} \\ & \mathrm{~V}_{\mathrm{DD}}=4.5 \mathrm{~V} \text { to } 5.5 \mathrm{~V} \end{aligned}$ |  | 0.4 | V |
| $\mathrm{V}_{\text {OL2 }}$ | Low-level output voltage 3 | $\begin{aligned} & \mathrm{I}_{\mathrm{OL}}=6 \mathrm{~mA} \\ & \mathrm{~V}_{\mathrm{DD}}=3.0 \mathrm{~V} \text { to } 3.6 \mathrm{~V} \end{aligned}$ |  | 0.4 | V |
| $\mathrm{V}_{\mathrm{OH} 1}$ | High-level output voltage ${ }^{3}$ | $\mathrm{I}_{\mathrm{OH}}=-8 \mathrm{~mA}$ <br> $\mathrm{V}_{\mathrm{DD}}$ from 4.5 V to 5.5 V | $0.7 \mathrm{~V}_{\mathrm{DD}}$ |  | V |
| $\mathrm{V}_{\mathrm{OH} 2}$ | High-level output voltage ${ }^{3}$ | $\mathrm{I}_{\mathrm{OH}}=-6 \mathrm{~mA}$ <br> $\mathrm{V}_{\mathrm{DD}}$ from 3.0 V to 3.6 V | 2.4 |  | V |
| $\mathrm{I}_{\text {OS1 }}$ | Short-circuit output current ${ }^{2,4}$ | $\mathrm{V}_{\mathrm{O}}=\mathrm{V}_{\mathrm{DD}}$ and $\mathrm{V}_{\mathrm{SS}}$ <br> $\mathrm{V}_{\mathrm{DD}}$ from 4.5 V to 5.5 V | -200 | +200 | mA |
| $\mathrm{I}_{\mathrm{OS} 2}$ | Short-circuit output current ${ }^{2,4}$ | $\mathrm{V}_{\mathrm{O}}=\mathrm{V}_{\mathrm{DD}}$ and $\mathrm{V}_{\mathrm{SS}}$ <br> $\mathrm{V}_{\mathrm{DD}}$ from 3.0 V to 3.6 V | -100 | +100 | mA |
| $\mathrm{I}_{\text {OL1 }}$ | Low level output current ${ }^{10}$ | $\begin{aligned} & \mathrm{V}_{\mathrm{IN}}=\mathrm{V}_{\mathrm{DD}} \text { or } \mathrm{V}_{\mathrm{SS}} \\ & \mathrm{~V}_{\mathrm{OL}}=0.4 \mathrm{~V} \\ & \mathrm{~V}_{\mathrm{DD}} \text { from } 4.5 \mathrm{~V} \text { to } 5.5 \mathrm{~V} \end{aligned}$ | +8 |  | mA |
| $\mathrm{I}_{\text {OL2 }}$ | Low level output current ${ }^{10}$ | $\begin{aligned} & \mathrm{V}_{\mathrm{IN}}=\mathrm{V}_{\mathrm{DD}} \text { or } \mathrm{V}_{\mathrm{SS}} \\ & \mathrm{~V}_{\mathrm{OL}}=0.4 \mathrm{~V} \\ & \mathrm{~V}_{\mathrm{DD}} \text { from } 3.0 \mathrm{~V} \text { to } 3.6 \mathrm{~V} \end{aligned}$ | +6 |  | mA |
| $\mathrm{I}_{\mathrm{OH} 1}$ | High level output current ${ }^{10}$ | $\begin{aligned} & \mathrm{V}_{\mathrm{IN}}=\mathrm{V}_{\mathrm{DD}} \text { or } \mathrm{V}_{\mathrm{SS}} \\ & \mathrm{~V}_{\mathrm{OH}}=\mathrm{V}_{\mathrm{DD}}-0.4 \mathrm{~V} \end{aligned}$ <br> $\mathrm{V}_{\mathrm{DD}}$ from 4.5 V to 5.5 V | -8 |  | mA |
| $\mathrm{I}_{\mathrm{OH} 2}$ | High level output current ${ }^{10}$ | $\begin{aligned} & \mathrm{V}_{\mathrm{IN}}=\mathrm{V}_{\mathrm{DD}} \text { or } \mathrm{V}_{\mathrm{SS}} \\ & \mathrm{~V}_{\mathrm{OH}}=\mathrm{V}_{\mathrm{DD}}-0.4 \mathrm{~V} \\ & \mathrm{~V}_{\mathrm{DD}} \text { from } 3.0 \mathrm{~V} \text { to } 3.6 \mathrm{~V} \end{aligned}$ | -6 |  | mA |


| $\mathrm{P}_{\text {total1 }}$ | Power dissipation $2,8,9$ | $\mathrm{C}_{\mathrm{L}}=50 \mathrm{pF}$ <br> $\mathrm{V}_{\mathrm{DD}}=4.5 \mathrm{~V}$ to 5.5 V | $\mathrm{mW} /$ <br> MHz |  |  |
| :---: | :--- | :--- | :---: | :---: | :---: |
| $\mathrm{P}_{\text {total2 }}$ | Power dissipation $2,8,9$ | $\mathrm{C}_{\mathrm{L}}=50 \mathrm{pF}$ <br> $\mathrm{V}_{\mathrm{DD}}=3.0 \mathrm{~V}$ to 3.6 V |  | 0.5 | $\mathrm{~mW} /$ |
| MHz |  |  |  |  |  |
| $\mathrm{I}_{\mathrm{DDQ}}$ | Quiescent Supply Current | $\mathrm{V}_{\mathrm{IN}}=\mathrm{V}_{\mathrm{DD}}$ or $\mathrm{V}_{\mathrm{SS}}$ <br> $\mathrm{V}_{\mathrm{DD}}$ from 3.6 V to 5.5 V |  |  |  |
| $\Delta \mathrm{I}_{\mathrm{DDQ}}$ | Quiescent Supply Current Delta | For input under test <br> $\mathrm{V}_{\mathrm{IN}}=\mathrm{V}_{\mathrm{DD}}-2.1 \mathrm{~V}$ <br> For all other inputs <br> $\mathrm{V}_{\mathrm{IN}}=\mathrm{V}_{\mathrm{DD}}$ or $\mathrm{V}_{\mathrm{SS}}$ <br> $\mathrm{V}_{\mathrm{DD}}=5.5 \mathrm{~V}$ | 25 | $\mu \mathrm{~A}$ |  |
| $\mathrm{C}_{\mathrm{IN}}$ | Input capacitance ${ }^{5}$ | $f=1 \mathrm{MHz}$ <br> $\mathrm{V}_{\mathrm{DD}}=5 \mathrm{~V}$ |  | 1.6 | mA |
| $\mathrm{C}_{\mathrm{OUT}}$ | Output capacitance ${ }^{5}$ | $f=1 \mathrm{MHz}$ <br> $\mathrm{V}_{\mathrm{DD}}=0 \mathrm{~V}$ |  | 15 | pF |

## Notes:

1. Functional tests are conducted in accordance with MIL-STD-883 with the following input test conditions: $\mathrm{V}_{\mathrm{IH}}=\mathrm{V}_{\mathrm{IH}}(\mathrm{min})+20 \%,-0 \% ; \mathrm{V}_{\mathrm{IL}}=\mathrm{V}_{\mathrm{IL}}(\max )+0 \%$, $50 \%$, as specified herein, for TTL, CMOS, or Schmitt compatible inputs. Devices may be tested using any input voltage within the above specified range, but are guaranteed to $\mathrm{V}_{\mathrm{IH}}(\min )$ and $\mathrm{V}_{\mathrm{IL}}$ (max).
2. Supplied as a design limit but not guaranteed or tested.
3. Per MIL-PRF-38535, for current density $\leq 5.0 \mathrm{E} 5 \mathrm{amps} / \mathrm{cm}^{2}$, the maximum product of load capacitance (per output buffer) times frequency should not exceed 3,765pF/ MHz.
4. Not more than one output may be shorted at a time for maximum duration of one second.
5. Capacitance measured for initial qualification and when design changes may affect the value. Capacitance is measured between the designated terminal and $\mathrm{V}_{\text {SS }}$ at frequency of 1 MHz and a signal amplitude of 50 mV rms maximum.
6. Maximum allowable relative shift equals 50 mV .
7. For devices procured with a total ionizing dose tolerance guarantee, the post-irradiation performance is guaranteed at $25^{\circ} \mathrm{C}$ per MIL-STD-883 method 1019 condition A up to the maximum TID level procured.
8. Power dissipation specified per switching output.
9. Power does not include power contribution of any TTL output sink current.
10. Guaranteed by characterization, but not tested.

AC ELECTRICAL CHARACTERISTICS FOR THE UT54ACTS00E ${ }^{2}$
( $\mathrm{V}_{\mathrm{DD}}=3.0 \mathrm{~V}$ to $5.5 \mathrm{~V} ; \mathrm{V}_{\mathrm{SS}}=0 \mathrm{~V}^{1} ;-55^{\circ} \mathrm{C}<\mathrm{T}_{\mathrm{C}}<+125^{\circ} \mathrm{C}$ )

| SYMBOL | PARAMETER | CONDITION | $\mathrm{V}_{\mathrm{DD}}$ | MINIMUM | MAXIMUM | UNIT |
| :---: | :---: | :---: | :---: | :---: | :---: | :---: |
| $\mathrm{t}_{\text {PLH }}$ | Input to Yn | $\mathrm{C}_{\mathrm{L}}=50 \mathrm{pF}$ | 4.5 V to 5.5 V | 1 | 8 | ns |
|  |  |  | 3.0 V to 3.6 V | 3 | 15 |  |
| $\mathrm{t}_{\text {PHL }}$ | Input to Yn | $\mathrm{C}_{\mathrm{L}}=50 \mathrm{pF}$ | 4.5 V to 5.5 V | 1 | 8 | ns |
|  |  |  | 3.0 V to 3.6 V | 3 | 15 |  |

## Notes:

1. Maximum allowable relative shift equals 50 mV .
2. For devices procured with a total ionizing dose tolerance guarantee, the post-irradiation performance is guaranteed at $25^{\circ} \mathrm{C}$ per MIL-STD-883 method 1019 condition A up to the maximum TID level procured.

## Packaging



|  | INC | MILLIME TER |
| :---: | :---: | :---: |
| DIM | MIN. MAX | MIN. MAX. |
| A | 0.0790 .101 | 2.0072 .575 |
| D | 0.0150 .019 | 0.3810 .483 |
| C | 0.0040 .006 | 0.1020 .152 |
| D | 0.3330 .347 | 8.4388 .814 |
| E | 0.2500 .260 | 6.3506 .604 |
| E 1 | 0.290 | 7.366 |
| E2 | 0.1700 .180 | 4.3184 .572 |
| E3 | 0.030 | 0.762 |
| e | 0.050 BSC | 1.270 BSC |
| L | 0.3400 .360 | 8.6369 .144 |
| 0 | 0.026 | 0.660 |
| S 1 | 0.005 | 0.127 |



SECTION A-A

Figure 1. 14 Lead Flatpack

## Ordering Information: UT54ACTS00E: SMD



Notes:

1. Lead finish (A,C, or X) must be specified.
2. If an " $X$ " is specified when ordering, part marking will match the lead finish and will be either "A" (solder) or "C" (gold).
3. Total dose radiation must be specified when ordering. QML Q and QML V not available without radiation hardening. For prototype inquiries, contact factory.
4. Device type 02 is only offered with a TID tolerance guarantee of $3 \mathrm{E} 5 \mathrm{rads}(\mathrm{Si})$ or $1 \mathrm{E} 6 \mathrm{rads}(\mathrm{Si})$ and is tested in accordance with MIL-STD-883 Test Method 1019 Condition A and section 3.11.2. Device type 03 is only offered with a TID tolerance guarantee of 1E5 rads(Si), 3E5 rads(Si), and 5E5 rads(Si), and is tested in accordance with MIL-STD-883 Test Method 1019 Condition A.
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Advanced Datasheet - Product In Development
Preliminary Datasheet - Shipping Prototype
Datasheet - Shipping QML & Reduced HiRel
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## Datasheet Revision History

| Revision Date | Description of Change |
| :--- | :---: |
| April 2015 | Initial Release of Datasheet |
| Version 1.0.0 |  |

